

NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE3420 uses advanced trench technology to provide excellent $R_{\rm DS(ON)}$, low gate charge and operation with gate voltages as low as 1.8V. This device is suitable for use as a uni-directional or bi-directional load switch.

General Features

• V_{DS} = 20V,I_D = 6A

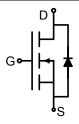
 $R_{DS(ON)}$ < 40m Ω @ V_{GS} =2.5V

 $R_{DS(ON)}$ < 33m Ω @ V_{GS} =4.5V

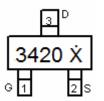
- High Power and current handing capability
- Surface Mount Package
- Pb free terminal plating
- RoHS compliant
- Halogen free

Application

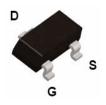
- Uni-directional Load switch
- Bi-directional Load switch



Schematic diagram



Marking and pin assignment



SOT-23 top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
3420 X	NCE3420	SOT-23	Ø180mm	8 mm	3000 units

Absolute Maximum Ratings (T_A=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	20	V
Gate-Source Voltage	V _{GS}	±12	V
Drain Current-Continuous	I _D	6	Α
Drain Current-Pulsed (Note 1)	I _{DM}	30	Α
Maximum Power Dissipation	P _D	1.25	W
Operating Junction and Storage Temperature Range	T_{J} , T_{STG}	-55 To 150	$^{\circ}$ C

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	R _{0JA}	100	°C/W
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Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	20	22	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =20V,V _{GS} =0V	-	-	1	μA



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Parameter	Symbol	Condition	Min	Тур	Max	Unit
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±12V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)	•	•	•			
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250μA	0.5	0.7	1.0	V
-i- O O Ot-t- Di-t	Б	V _{GS} =2.5V, I _D =4.0 A	-	21	40	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _D =5.0A	-	18	33	mΩ
Forward Transconductance	g FS	V_{DS} =5 V , I_{D} =5 A	-	25	-	S
Dynamic Characteristics (Note4)	•	•	•			
Input Capacitance	C _{lss}	\/ 40\/\/ 0\/	-	424.5	-	PF
Output Capacitance	Coss	$V_{DS}=10V, V_{GS}=0V,$	-	59.5	-	PF
Reverse Transfer Capacitance	C _{rss}	- F=1.0MHz	-	51.5	-	PF
Switching Characteristics (Note 4)	<u>.</u>					
Turn-on Delay Time	t _{d(on)}	V_{DD} =10V, R_L =2 Ω V_{GS} =10V, R_{GEN} =3 Ω	-	3	-	nS
Turn-on Rise Time	t _r		-	7.5	-	nS
Turn-Off Delay Time	t _{d(off)}		-	20	-	nS
Turn-Off Fall Time	t _f		-	6	-	nS
Total Gate Charge	Qg		-	12	-	nC
Gate-Source Charge	Q _{gs}	V _{DS} =10V,I _D =5A,V _{GS} =10V	-	1	-	nC
Gate-Drain Charge	Q_{gd}]	-	2	-	nC
Drain-Source Diode Characteristics			•			•
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =5A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	6	Α

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- **3.** Pulse Test: Pulse Width ≤ 300μ s, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics

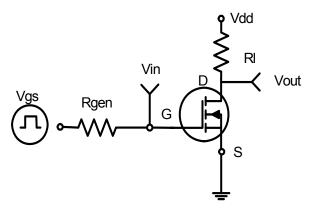


Figure 1:Switching Test Circuit

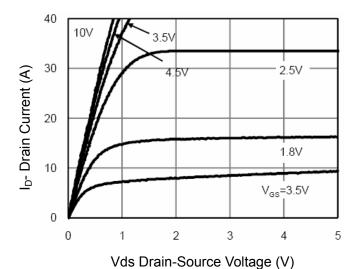


Figure 3 Output Characteristics

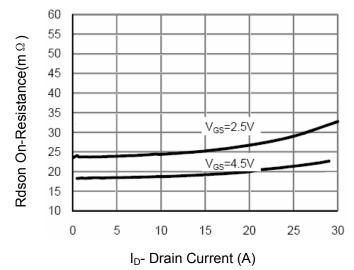


Figure 5 Drain-Source On-Resistance

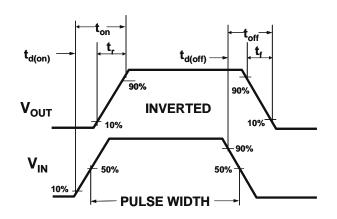


Figure 2:Switching Waveforms

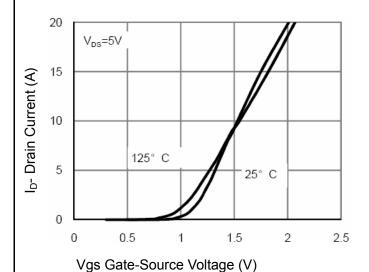


Figure 4 Transfer Characteristics

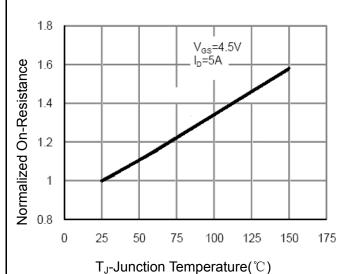
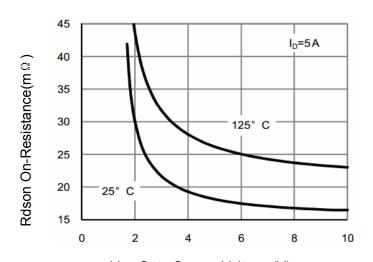
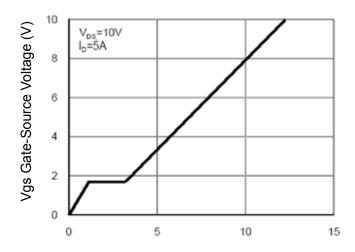


Figure 6 Drain-Source On-Resistance





Vgs Gate-Source Voltage (V)
Figure7 Rdson vs Vgs



Qg Gate Charge (nC) Figure 9 Gate Charge

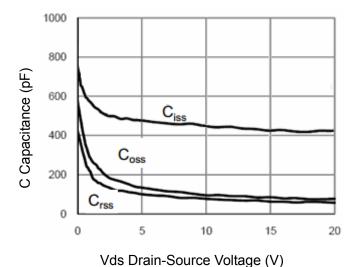
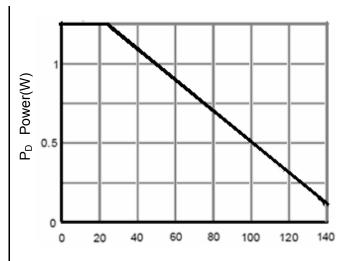


Figure 11 Capacitance vs Vds



T_J-Junction Temperature(°C)

Figure 8 Power Dissipation

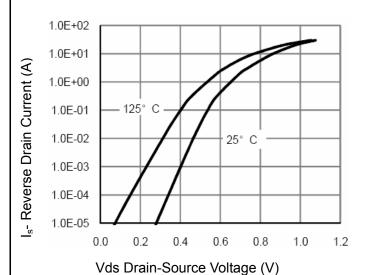
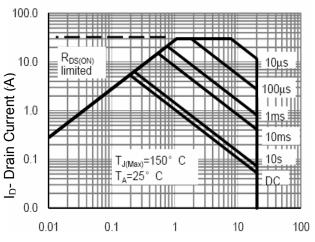


Figure 10 Source- Drain Diode Forward



Vds Drain-Source Voltage (V)

Figure 12 Safe Operation Area



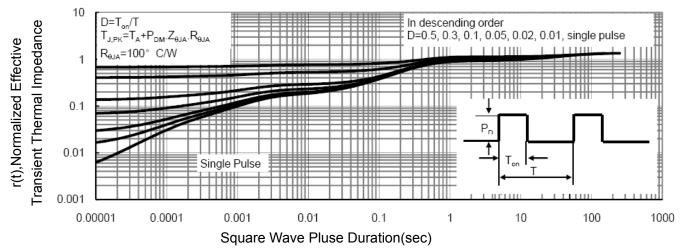
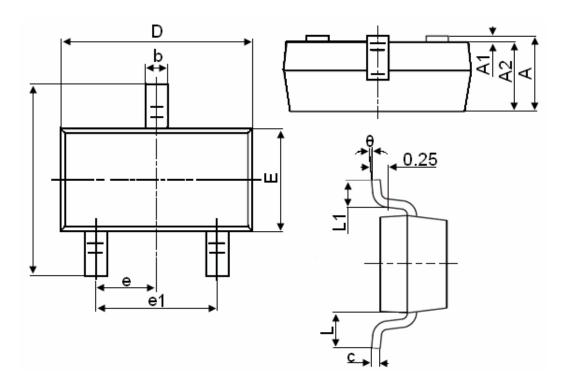


Figure 13 Normalized Maximum Transient Thermal Impedance



SOT-23 Package Information



Symbol	Dimensions in Millimeters				
Symbol	MIN.	MAX.			
Α	0.900	1.150			
A1	0.000	0.100			
A2	0.900	1.050			
b	0.300	0.500			
С	0.080	0.150			
D	2.800	3.000			
Е	1.200	1.400			
E1	2.250	2.550			
e 0.950TYP		0.950TYP			
e1	1.800	2.000			
L	0.550REF				
L1	0.300	0.500			
θ	0°	8°			

Notes

- 1. All dimensions are in millimeters.
- 2. Tolerance ±0.10mm (4 mil) unless otherwise specified
- 3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
- 4. Dimension L is measured in gauge plane.
- $5. \ Controlling \ dimension \ is \ millimeter, \ converted \ inch \ dimensions \ are \ not \ necessarily \ exact.$



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